



STW11NK100Z

N-CHANNEL 1000V - 1.1Ω - 8.3A TO-247 Zener-Protected SuperMESH™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STW11NK100Z	1000 V	< 1.38 Ω	8.3 A	230 W

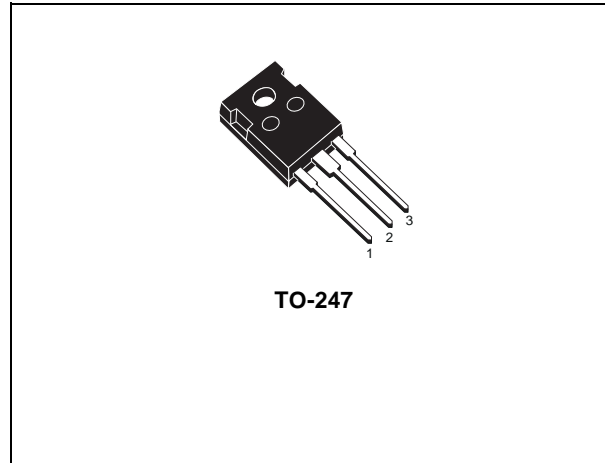
- TYPICAL R_{DS(on)} = 1.1 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

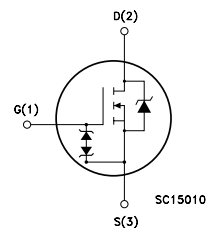
APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES



TO-247

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STW11NK100Z	W11NK100Z	TO-247	TUBE

STW11NK100Z

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	1000	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	1000	V
V _{GS}	Gate- source Voltage	± 30	V
I _D	Drain Current (continuous) at T _C = 25°C	8.3	A
I _D	Drain Current (continuous) at T _C = 100°C	5.2	A
I _{DM} (•)	Drain Current (pulsed)	33.2	A
P _{TOT}	Total Dissipation at T _C = 25°C	230	W
	Derating Factor	1.85	W/°C
V _{ESD(G-S)}	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	6000	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T _j T _{stg}	Operating Junction Temperature Storage Temperature	-55 to 150	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 8.3A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

(*) Limited only by maximum temperature allowed

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case Max	0.54	°C/W
R _{thj-amb} T _I	Thermal Resistance Junction-ambient Max Maximum Lead Temperature For Soldering Purpose	50 300	°C/W °C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	8.3	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	550	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{GSO}	Gate-Source Breakdown Voltage	I _{gs} =± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 100 \mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V, I_D = 4.15 \text{ A}$		1.1	1.38	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15 \text{ V}, I_D = 4.15 \text{ A}$		9		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		3500 270 60		pF pF pF
$C_{oss \text{ eq.}} (3)$	Equivalent Output Capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 500V$		170		pF
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time	$V_{DD} = 800 \text{ V}, I_D = 8 \text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		27 18 98 55		ns ns ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 800V, I_D = 8 \text{ A},$ $V_{GS} = 10V$		113 18 60	162	nC nC nC

SOURCE DRAIN DIODE

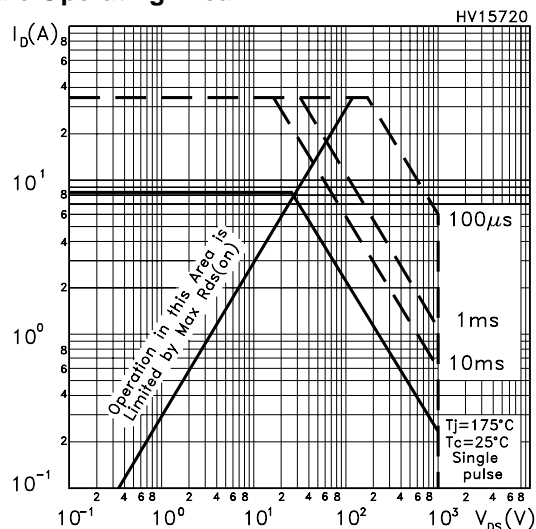
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				8.3 33.2	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 8.3 \text{ A}, V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 8 \text{ A}, di/dt = 100 \text{ A}/\mu s$ $V_{DD} = 80 \text{ V}, T_j = 25^{\circ}C$ (see test circuit, Figure 5)		560 4.48 16		ns μC A
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 8 \text{ A}, di/dt = 100 \text{ A}/\mu s$ $V_{DD} = 80 \text{ V}, T_j = 150^{\circ}C$ (see test circuit, Figure 5)		620 4.57 16		ns μC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

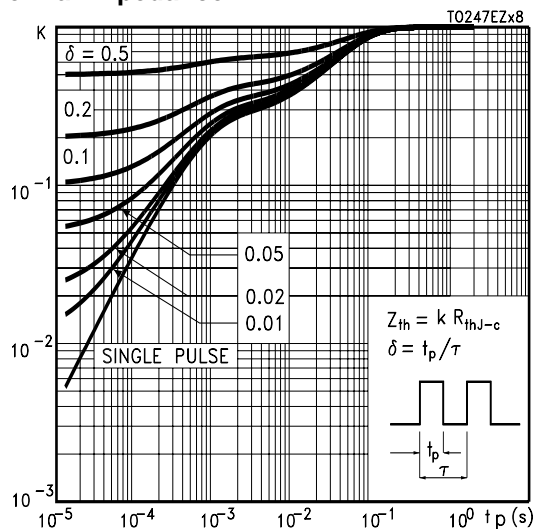
2. Pulse width limited by safe operating area.

3. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

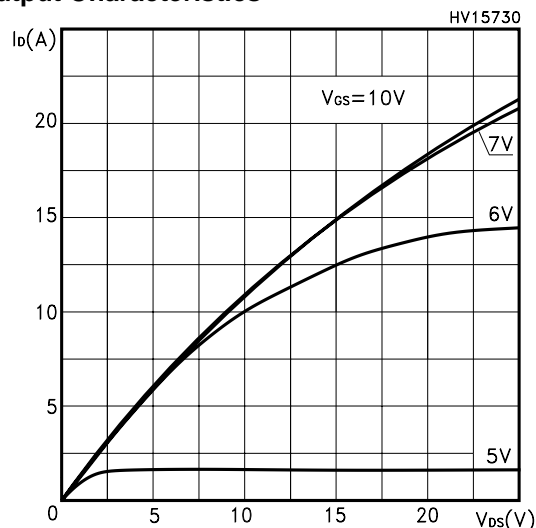
Safe Operating Area



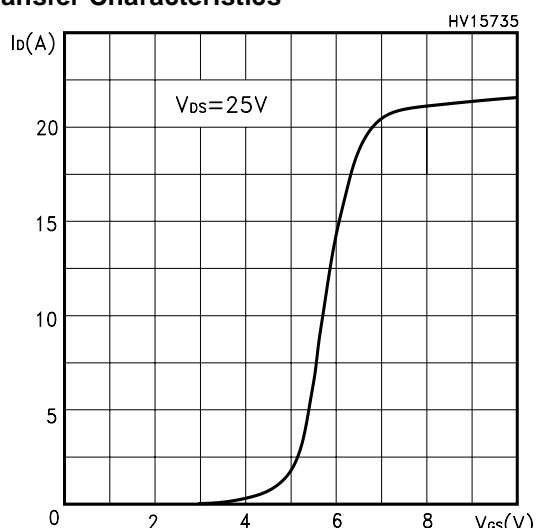
Thermal Impedance



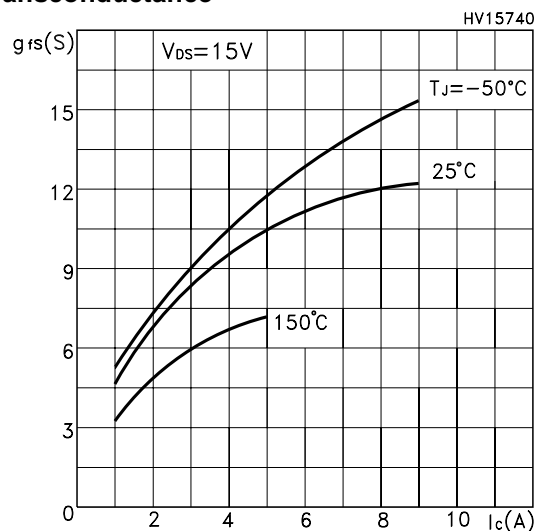
Output Characteristics



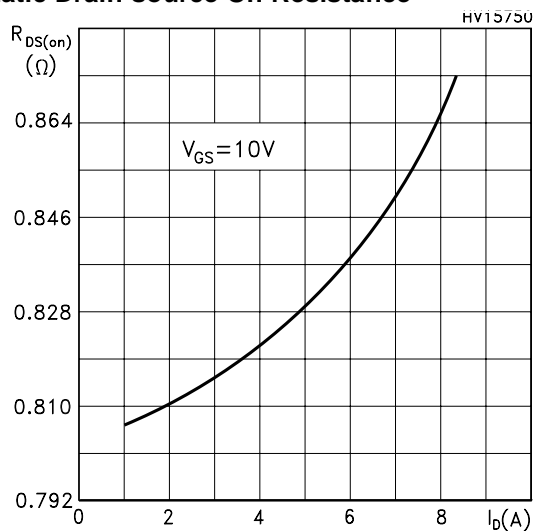
Transfer Characteristics



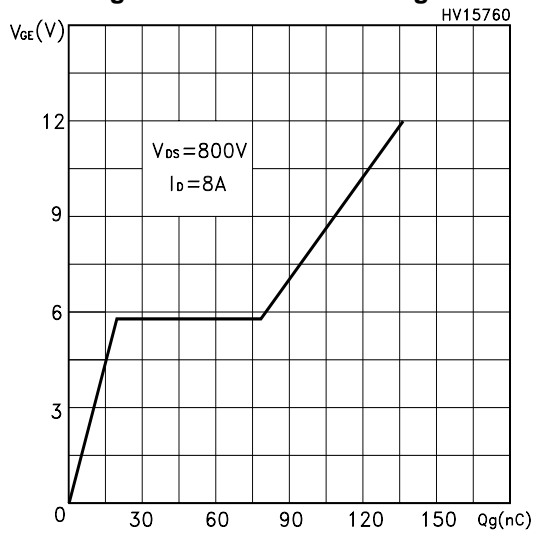
Transconductance



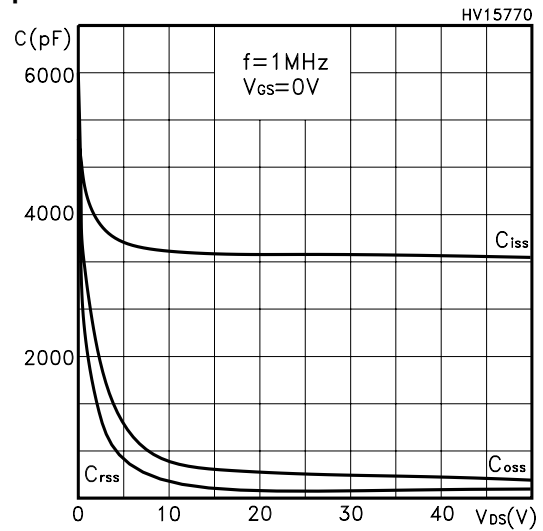
Static Drain-source On Resistance



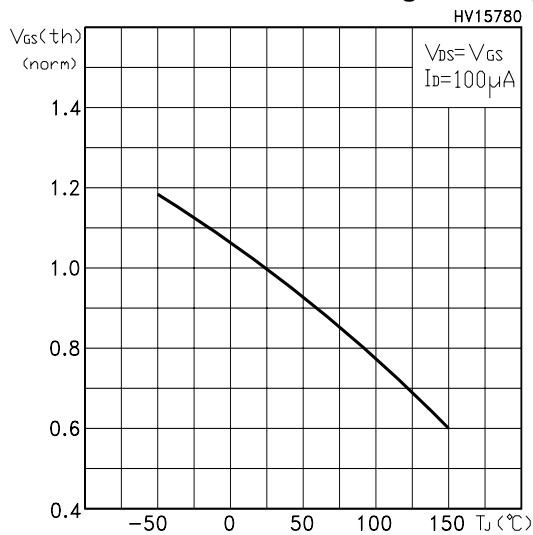
Gate Charge vs Gate-source Voltage



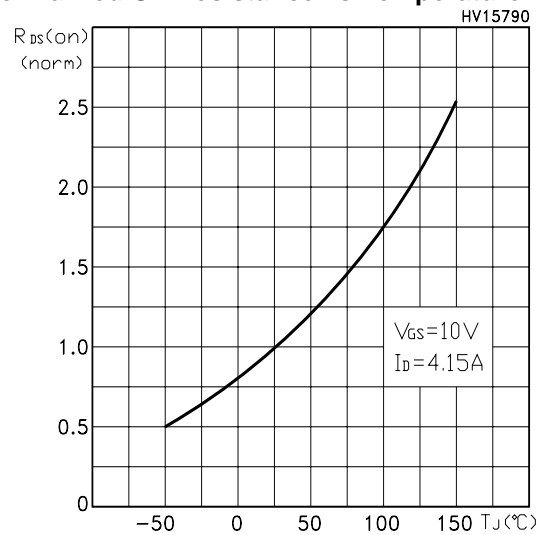
Capacitance Variations



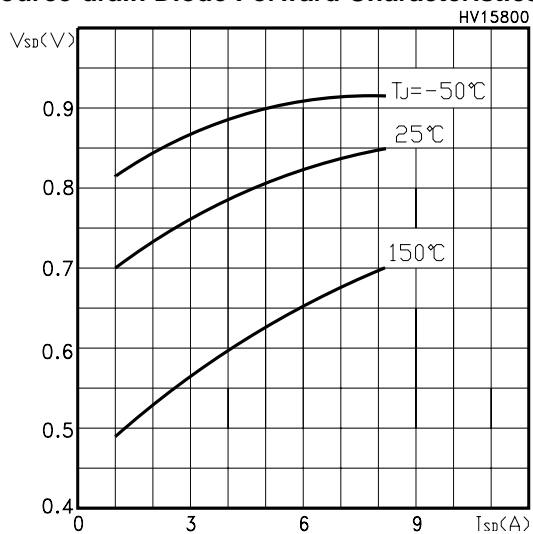
Normalized Gate Threshold Voltage vs Temp.



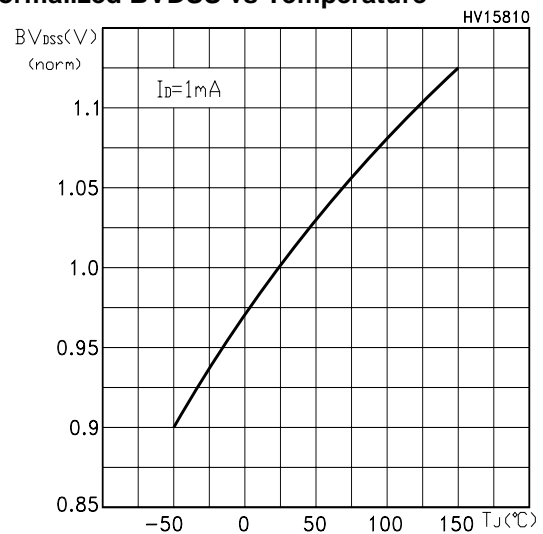
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Maximum Avalanche Energy vs Temperature

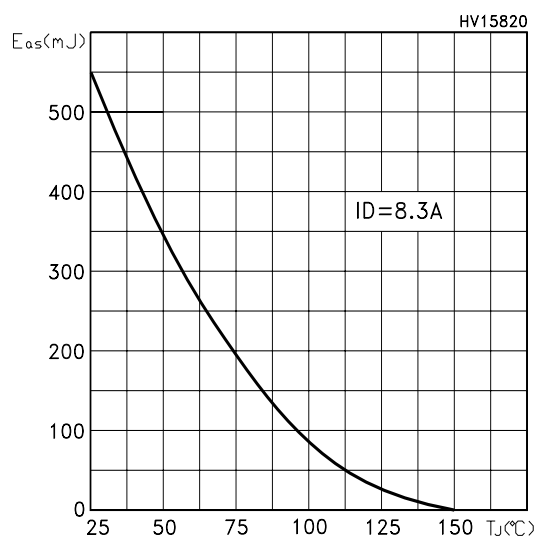


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

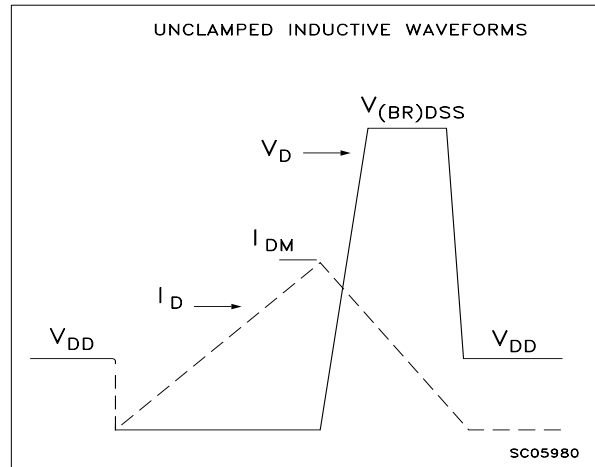


Fig. 3: Switching Times Test Circuit For Resistive Load

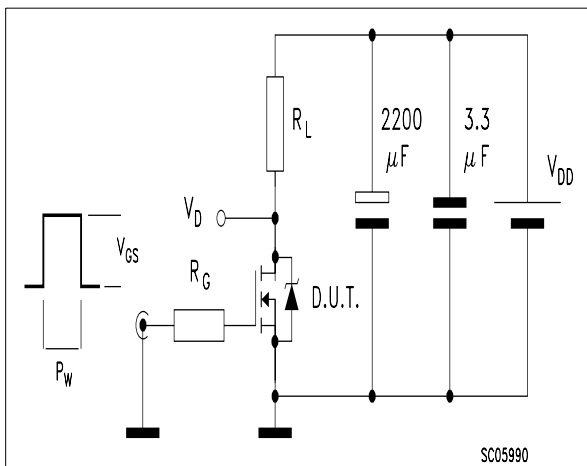


Fig. 4: Gate Charge test Circuit

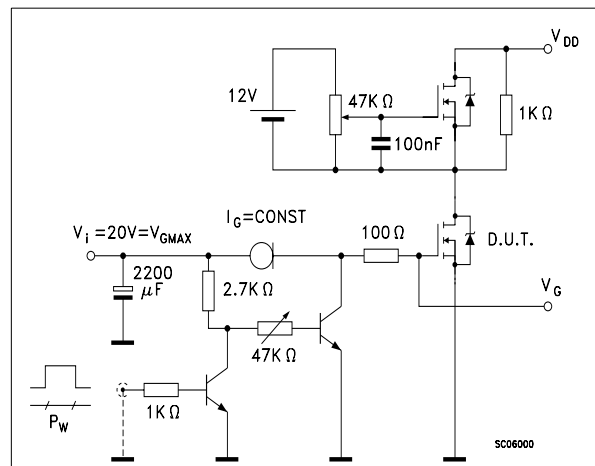
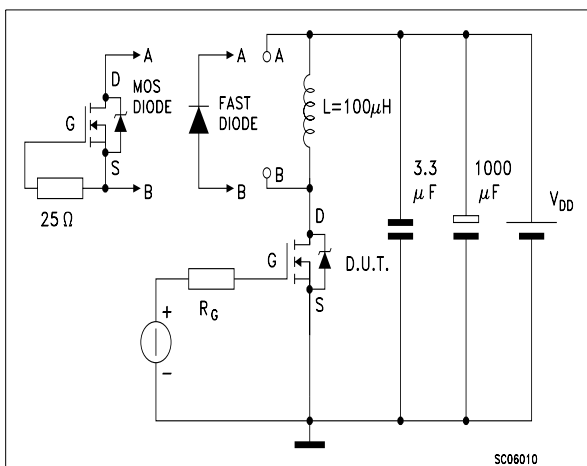
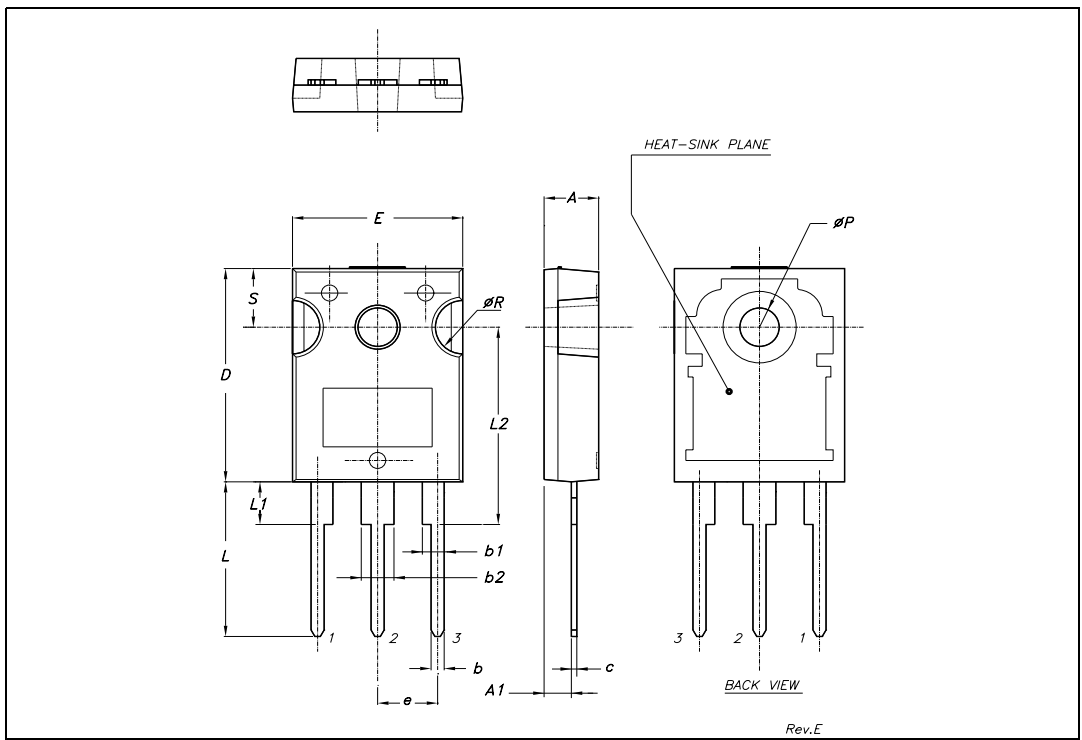


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



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